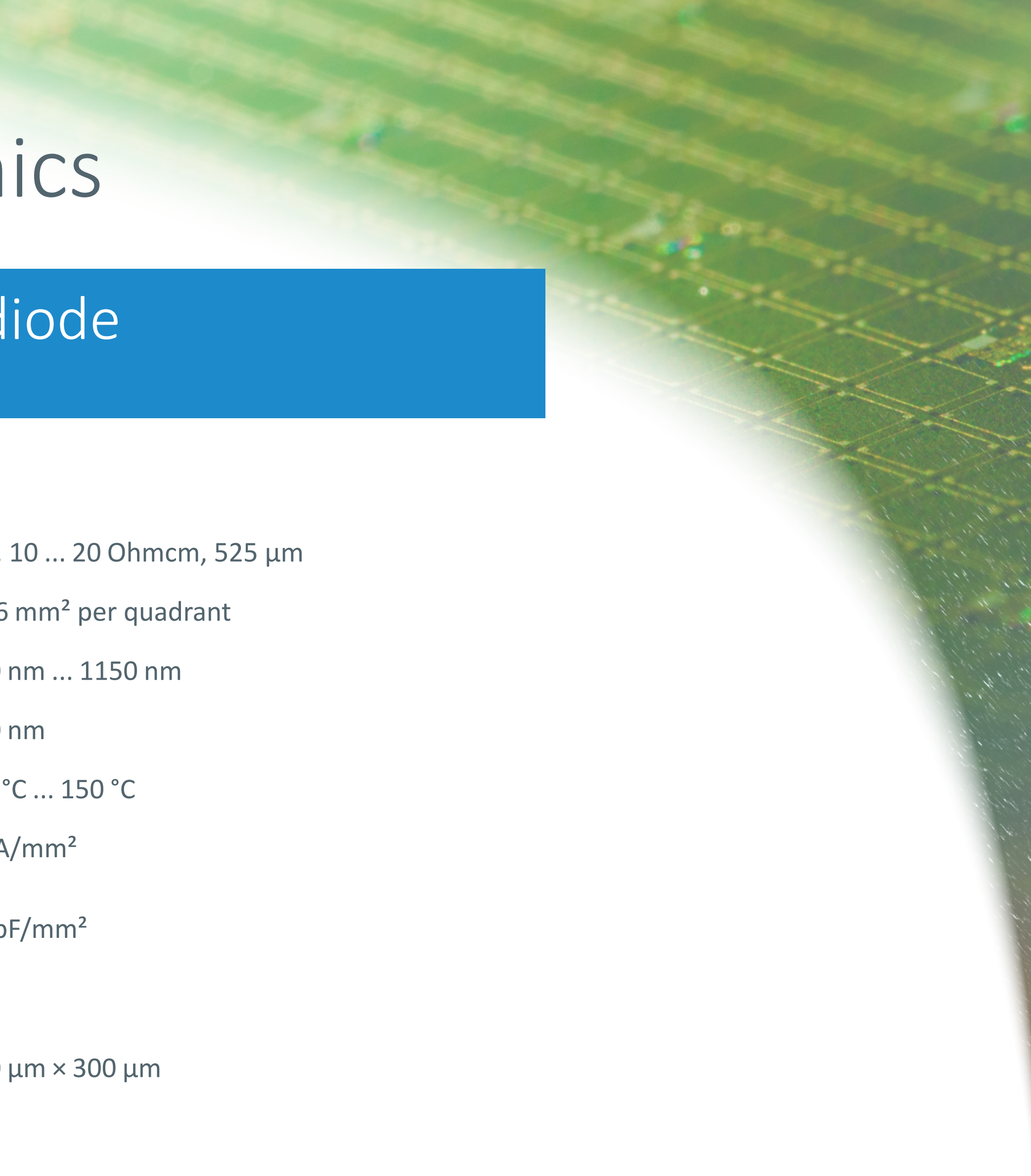
ifw optronics



8 Octands photodiode
with hole

Specifications

Detection material:	n/P, 10 ... 20 Ohmcm, 525 µm
Active area:	5.36 mm² per quadrant
Spectral range:	200 nm ... 1150 nm
Wavelength of peak response:	800 nm
Storage temperature:	-40 °C ... 150 °C
Dark current I_R: (max at -5 V)	2 nA/mm²
Junction capacitance C_j: (max at -5 V)	30 pF/mm²
Top bondpad material:	AlSi
Top bondpad size:	300 µm × 300 µm
Bottom material:	AlSi